REMARKS

Claims 1, 3, 4, and 9 are now pending in the application. The Examiner is respectfully requested to reconsider and withdraw the rejection in view of the amendments and remarks contained herein.

REJECTION UNDER 35 U.S.C. § 102

Claims 1, 3, 4, and 9 stand rejected under 35 U.S.C. § 102(e) as being anticipated by Adan (U.S. Pat. No. 6,288,425). This rejection is respectfully traversed.

Adan is directed generally towards a silicon-on-insulator field effect transistor. The transistor includes a gate region formed on a semiconductor layer. A source region and a drain region are spaced apart by a channel region.

Claim 1 calls for source and drain regions of a first conductive type and a channel region of a second conductive type. In contrast, Adan includes a channel region 5 having a fully depleted surface channel (P-type) with a specific impurity concentration that separates the extension regions from an N-type embedded region. As such, no channel region of a second conductive type is provided.

Claim 9 calls for a semiconductor film having a film thickness of 50 nm or less. In contrast, Adan includes a semiconductor film having a film thickness of 100 to 500 nm and an N-type embedded region film having a thickness of 50 to 450 nm. If a film thickness of the semiconductor film is 50 nm or less, it cannot accommodate an N-type embedded region because the drain region, the N-type embedded region and the source region fall short. In other words, Adan teaches directly away form a semiconductor film having a film thickness of 50 nm or less.

Therefore, Applicant respectfully submits that Adan does not teach the present

invention.

CONCLUSION

It is believed that all of the stated grounds of rejection have been properly

traversed, accommodated, or rendered moot. Applicant therefore respectfully requests

that the Examiner reconsider and withdraw all presently outstanding rejections. It is

believed that a full and complete response has been made to the outstanding Office

Action, and as such, the present application is in condition for allowance. Thus, prompt

and favorable consideration of this amendment is respectfully requested.

If the Examiner believes that personal communication will expedite prosecution

of this application, the Examiner is invited to telephone the undersigned at (248) 641-

1600.

Respectfully submitted,

Dated:

July 19, 2004

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